## NSN 5961-01-247-8315

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-247-8315 **Inclosure Material:** Metal **Overall Length: 7.578** inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-205 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case and quality assurance level txv **Overall Width Across Flats:** 1.250 inches **Thread Size:** 0.750 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 144.0 nonrepetitive peak reverse voltage and 1200.0 working peak reverse voltage, peak total value **Current Rating Per Characteristic:** 200.00 amperes forward current, average absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 case **Specification Data:** 81349-mil-s-19500/211 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** 

No

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